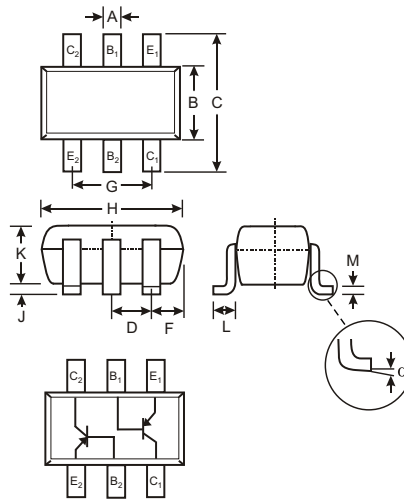


**Features**

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)

**Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K3N
- Ordering Information: See Below
- Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J		0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
	0°	8°
All Dimensions in mm		

**Maximum Ratings** @ TA = 25 C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous	I <sub>C</sub>	-200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient	R <sub>JA</sub>	625	C/W
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	C

**Ordering Information** (Note 2)

Device	Packaging	Shipping
MMDT3906-7-F	SOT-363	3000/Tape & Reel

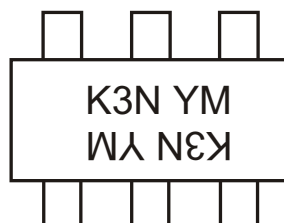
- Notes:
- Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  - For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
  - No purposefully added lead.

## Electrical Characteristics @ T<sub>A</sub> = 25 C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40		V	I <sub>C</sub> = -10 A, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-40		V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0		V	I <sub>E</sub> = -10 A, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>		-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
Base Cutoff Current	I <sub>BL</sub>		-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
<b>ON CHARACTERISTICS (Note 4)</b>					
DC Current Gain	h <sub>FE</sub>	60 80 100 60 30	300		I <sub>C</sub> = -100μA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -50mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -100mA, V <sub>CE</sub> = -1.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		-0.25 -0.40	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65	-0.85 -0.95	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>		4.5	pF	V <sub>CB</sub> = -5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>		10	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	2.0	12	k	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	100	400		
Output Admittance	h <sub>oe</sub>	3.0	60	S	
Current Gain-Bandwidth Product	f <sub>T</sub>	250		MHz	
Noise Figure	NF		4.0	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -100 A, R <sub>S</sub> = 1.0k f = 1.0kHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>d</sub>		35	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, V <sub>BE(off)</sub> = 0.5V, I <sub>B1</sub> = -1.0mA
Rise Time	t <sub>r</sub>		35	ns	
Storage Time	t <sub>s</sub>		225	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, I <sub>B1</sub> = I <sub>B2</sub> = -1.0mA
Fall Time	t <sub>f</sub>		75	ns	

Notes: 4. Short duration test pulse used to minimize self-heating.

## Marking Information



K3N = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

### Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

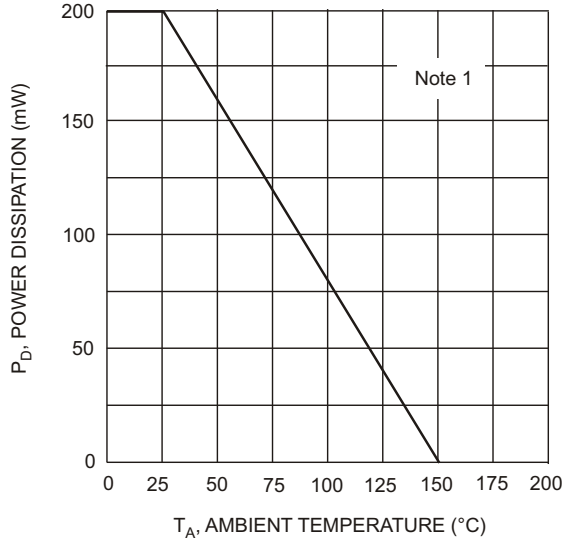


Fig. 1, Max Power Dissipation vs Ambient Temperature

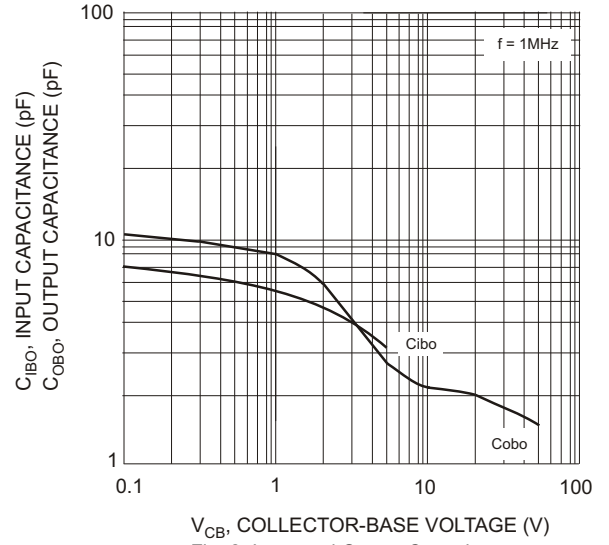


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

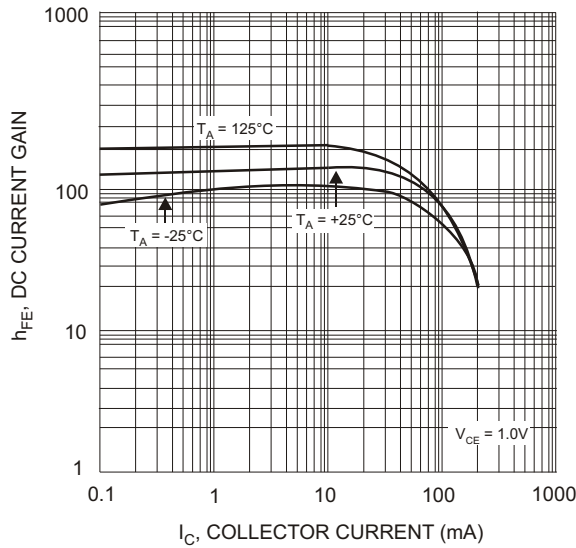


Fig. 3, Typical DC Current Gain vs Collector Current

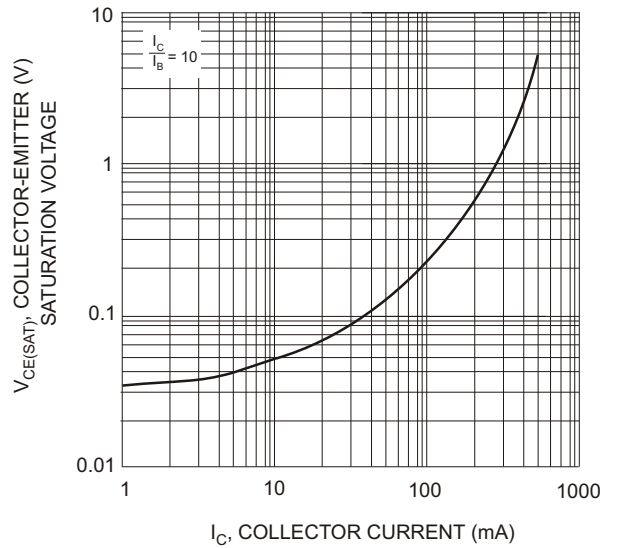


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

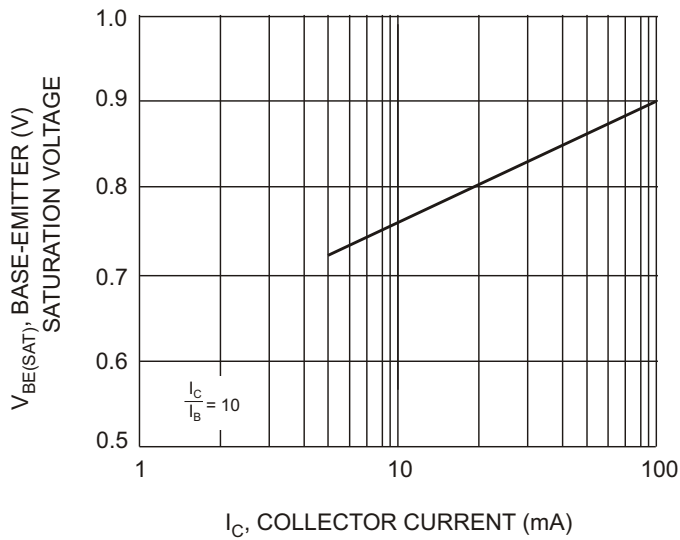


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



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